L Number	Hits	Search Text	DB	Time stamp
3	1480	(257/316).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO;	2004/03/18 16:52
6	474	(257/303).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18 16:52
7	155	(257/929).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18 16:53
8	51	(438/222).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18
9	876	(257/368).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18
10	42	(257/41).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18 16:54
11	34	(257/44).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18
12	751	(257/288).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18 16:57
13	732	(257/592).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18
14	242	(438/350).ccls. and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2004/03/18 16:57
-	10	(("5393681") or ("6391692") or ("5308782") or ("5998248") or ("6319782")).PN.	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/06/25 06:43
-	162	257/929 and @ad<=20010323	DERWENT; IBM_TDB USPAT; US-PGPUB;	2003/06/24 14:45
-	542	438/300 and @ad<=20010323	EPO; JPO; DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2003/06/24
-	4	@ad<=20010323 and 'raised vertical lateral transistor'	DERWENT; IBM_TDB USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/04 16:02

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			. W.	
_	1	@ad<=20010323 and 'raised source and drain'	USPAT; US-PGPUB;	2002/09/04 15:26
			EPO; JPO; DERWENT; IBM TDB	
-	1	@ad<=20010323 and 'epitaxial' and 'source	USPAT;	2002/09/04
		or drain'	US-PGPUB;	15:30
			EPO; JPO; DERWENT; IBM TDB	
_	8	@ad<=20010323 and 'epitaxial' and 'source	USPĀT;	2002/09/04
		and drain'	US-PGPUB; EPO; JPO;	15:30
			DERWENT; IBM TDB	
_	3470	gardner.inv.	USPAT;	2002/09/04
			US-PGPUB;	15:45
			EPO; JPO; DERWENT;	
	_		IBM_TDB	
-	6	gardner.inv. and 'vertical transistor' and @ad<=20010323	USPAT; US-PGPUB;	2002/09/04 15:48
			EPO; JPO;	
			DERWENT; IBM TDB	
_	4	@ad<=20010323 and 'elevated source and	USPAT;	2003/03/25
		drain'	US-PGPUB; EPO; JPO;	14:24
			DERWENT;	
	257	 @ad<=20010323 and 'elevated source'	IBM_TDB USPAT;	2002/09/04
	237	dad = 20010323 and elevated source	US-PGPUB;	16:06
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	37	<pre>@ad<=20010323 and 'epitaxial' with 'elevated source'</pre>	USPAT; US-PGPUB;	2003/06/24
		relevated source	EPO; JPO;	14:23
			DERWENT; IBM TDB	·
_	1	"4728623".PN.	USPAT	2002/09/04
_	1	 "4738937".PN.	USPAT	16:31 2002/09/04
				16:31
-	1	"4918029".PN.	USPAT	2002/09/04 16:31
-	1	"5004702".PN.	USPAT	2002/09/04
_	1	"5030583".PN.	USPAT	2002/09/04
_	1	"5032538".PN.	USPAT	2002/09/04
_	1	"5045494".PN.	USPAT	2002/09/04 16:31
-	1	"5272109".PN.	USPAT	2002/09/04
-	1	"5496750".PN.	USPAT	2002/09/04
-	1	"5378651".PN.	USPAT	2002/09/04
-	1	"5321306".PN.	USPAT	2002/09/04
-	1	"5296388".PN.	USPAT	2002/09/04
-	1	"5250454".PN.	USPAT	2002/09/04
_	1	"5213991".PN.	USPAT	2002/09/04
-	1	"5079180".PN.	USPAT	2002/09/04
-	1	"5057899".PN.	USPAT	2002/09/04
L	L		L	10.39

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<u> </u>	1	"4966861".PN.	USPAT	2002/09/04
	_			16:41
-	1	"4814841".PN.	USPAT	2002/09/04 16:48
-	1	"5057893".PN.	USPAT	2002/09/04 16:48 ·
-	18	(("6096596") or ("6090691") or ("6057200") or ("6001697") or ("5998844") or ("5963822") or ("5945698") or	USPAT; US-PGPUB; EPO; JPO;	2002/09/05 08:23
		("5933738") or ("5863826")).PN.	DERWENT; IBM_TDB	
-	18	("5641694") or ("5600161") or ("5497017") or ("5312768") or ("5156987") or	USPAT; US-PGPUB; EPO; JPO;	2002/09/05
		("5122476") or ("5087586")).PN.	DERWENT; IBM_TDB	2000/00/05
_	2	("5308782").PN.	USPAT; US-PGPUB; EPO; JPO;	2002/09/05
-	2	("6319782").PN.	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/09/05
			EPO; JPO; DERWENT; IBM_TDB	10.19
-	1731	((438/300) or (257/302) or (257/929) or (257/592)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20
-	12	ri-seiko.in.	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/20
_	38	<pre>@ad<=20010323 and 'epitaxial' with 'elevated source'</pre>	DERWENT; IBM_TDB USPAT; US-PGPUB;	2002/11/20 09:33
	263	@ad<=20010323 and 'elevated source'	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/11/20
	203	eaux-20010323 and elevated source	US-PGPUB; EPO; JPO; DERWENT;	09:33
_	263	@ad<=20010323 and elevated adj1 source	IBM_TDB USPAT; US-PGPUB; EPO; JPO;	2002/11/20
_	95	@ad<=20010323 and elevated adj1 drain	DERWENT; IBM_TDB USPAT;	2002/11/20
			US-PGPUB; EPO; JPO; DERWENT; IBM TDB	09:02
-	112	@ad<=20010323 and raised adj1 drain	USPAT; US-PGPUB; EPO; JPO; DERWENT;	2002/11/20
-	229	@ad<=20010323 and raised adj1 source	IBM_TDB USPAT; US-PGPUB;	2002/11/20 09:03
_	o	@ad<=20010323 and 'epitaxial silicon	EPO; JPO; DERWENT; IBM_TDB USPAT;	2002/11/20
	,	gate' with 'elevated source'	US-PGPUB; EPO; JPO; DERWENT;	09:38
			IBM TDB	

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-	20	- -	USPAT;	2002/11/20
		'elevated source'	US-PGPUB;	09:38
			EPO; JPO;	
]			DERWENT;	
İ			IBM TDB	
-	47	@ad<=20010323 and 'polysilicon gate' and	USPAT;	2003/03/25
		'elevated source'	US-PGPUB;	14:14
		02014004 004200	EPO; JPO;	1
			DERWENT;	
			1	i
			IBM_TDB	0000/00/05
-	0	• · · · · · · · · · · · · · · · · · ·	USPAT;	2003/03/25
		gate' and 'elevated source'	US-PGPUB;	14:25
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	1	<pre>@ad<=20010323 and 'epitaxial polysilicon'</pre>	USPAT;	2002/11/20
		and 'elevated source'	US-PGPUB;	10:08
			EPO; JPO;	
			DERWENT;]
			IBM TDB	
	56	And -20010222 and tonitavial 1.	USPAT;	2002/11/21
-] 56	@ad<=20010323 and 'epitaxial polysilicon'	1	1 ' '
1			US-PGPUB;	08:20
			EPO; JPO;	·
			DERWENT;	
			IBM_TDB	
-	0	@ad<=20010323 and 'epitaxial polysilicon	USPAT;	2002/11/20
		gate'	US-PGPUB;	14:05
		9400	EPO; JPO;	
			DERWENT;	
			IBM TDB	
		0-44,20010222 1 1 1 1 1		2002/11/20
_	24	@ad<=20010323 and 'epitaxial gate'	USPAT;	
			US-PGPUB;	14:05
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
_	24	@ad<=20010323 and 'epitaxial gate'	USPAT;	2002/11/21
			US-PGPUB;	08:30
	•		EPO; JPO;	
			DERWENT;	
	5.60	0-4, 20010222	IBM_TDB	2002/11/20
-	560		USPAT;	
	i	epitaxial with gate	US-PGPUB;	16:16
			EPO; JPO;	
			DERWENT;	
		•	IBM_TDB	
-	2348	@ad<=20010323 and 'multilayer' same	USPAT;	2002/11/21
		'gate'	US-PGPUB;	08:55
		9	EPO; JPO;	
			DERWENT;	
			IBM TDB	
]	200	(And -20010222 and Invited!	USPAT;	2002/11/20
-	260		1	2002/11/20
		'gate') and 'epitaxial'	US-PGPUB;	16:18
1			EPO; JPO;	
!			DERWENT;]
I			IBM_TDB	
l –	0	<pre>@ad<=20010323 and 'multilayer gate' with</pre>	USPĀT;	2003/06/25
1		'epitaxial'	US-PGPUB;	08:33
1		· · · · · · · · · · · · · · · · · · ·	EPO; JPO;	j l
[DERWENT;	
			IBM TDB	
	,		USPAT;	2002/11/21
-	1			
		near polysilicon	US-PGPUB;	08:20
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	693	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2002/11/21
		same 'gate'	US-PGPUB;	08:32
			EPO; JPO;	
			DERWENT;	
	1	1	IBM TDB	ı

	,			
-	367	<pre>@ad<=20010323 and 'epitaxial silicon' with 'gate'</pre>	USPAT; US-PGPUB;	2002/11/21 08:41
	1		EPO; JPO;	
			DERWENT; IBM TDB	·
_	9	@ad<=20010323 and 'epitaxial silicon	USPAT;	2003/03/26
		gate'	US-PGPUB;	10:14
			EPO; JPO;	
			DERWENT; IBM TDB	
-	1	@ad<=20010323 and 'multilayer silicon	USPAT;	2002/11/21
		gate'	US-PGPUB;	08:56
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	1	("6534809").PN.	USPAT; US-PGPUB;	2003/03/25
			EPO; JPO;	13.33
			DERWENT;	
	564	@ad<=20010323 and 'polysilicon gate' same	IBM_TDB USPAT;	2003/03/25
	304	'epitaxial'	US-PGPUB;	14:18
			EPO; JPO;	
			DERWENT; IBM_TDB	
_	390	(257/756).ccls and @ad<=20010323	USPAT;	2003/06/24
			US-PGPUB;	14:43
			EPO; JPO; DERWENT;	
			IBM_TDB	
_	214	@ad<=20010323 and 'floating gate' same	USPAT;	2003/03/25 14:18
		'epitaxial'	US-PGPUB; EPO; JPO;	14:18
			DERWENT;	
	2141	@ad<=20010323 and 'elevated' same	IBM_TDB USPAT;	2003/03/25
-	2141	'source' and 'drain'	US-PGPUB;	14:28
			EPO; JPO;	
			DERWENT; IBM TDB	
_	413	@ad<=20010323 and 'elevated' with	USPAT;	2003/03/25
		'source' with 'drain'	US-PGPUB;	14:28
			EPO; JPO; DERWENT;	
			IBM TDB	
-	6	@ad<=20010323 and 'epi silicon' and	USPAT;	2003/06/25
		'elevated' same 'source'	US-PGPUB; EPO; JPO;	06:45
			DERWENT;	
	1	"4074300".PN.	IBM_TDB USPAT	2003/03/25
		- 40/4000 .EM.	JUDIAL	14:37
-	32	@ad<=20010323 and 'gate stack' and	USPAT;	2003/03/25
		'elevated' same 'source'	US-PGPUB; EPO; JPO;	15:13
			DERWENT;	
		//!/4E9210E!!\ om /!!609291E!!\ -~	IBM_TDB	2003/03/25
_	8	(("4583105") or ("6083815") or ("5885877") or ("5986328")).PN.	USPAT; US-PGPUB;	15:39
		, , , , , , , , , , , , , , , , , , , ,	EPO; JPO;	
			DERWENT; IBM TDB	
_	2	("5198378").PN.	USPAT;	2003/03/25
			US-PGPUB;	15:39
			EPO; JPO; DERWENT;	
			IBM_TDB	
-	92	<pre>@ad<=20010323 and 'epi' and 'silicon gate'</pre>	USPAT;	2003/03/26
		yace	US-PGPUB; EPO; JPO;	11:54
			DERWENT;	
	L		IBM TDB	

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-	9	@ad<=20010323 and 'epitaxial silicon	USPAT;	2003/03/26
		gate'	US-PGPUB;	11:10
			EPO; JPO;	
			DERWENT;	
	1	/"6529262"\ DN	IBM_TDB	2003/03/26
_	1	("6528363").PN.	USPAT; US-PGPUB;	11:10
			EPO; JPO;	11.10
			DERWENT;	
			IBM TDB	
_	7	@ad<=20010323 and 'conductor' same 'epi'	USPAT;	2003/03/26
	·	same 'polysilicon' same 'amorphous'	US-PGPUB;	14:31
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	0	@ad<=20010323 and 'conductive' same 'epi'	USPAT;	2003/03/26
		same 'polysilicon' same 'amorphous'	US-PGPUB;	12:04
			EPO; JPO;	
			DERWENT;	·
			IBM_TDB	
-	3	("6335251").PN.	USPAT;	2003/03/26
			US-PGPUB;	14:34
			EPO; JPO;	
			DERWENT;	
		/# cooo c 4 d # \ _ =	IBM_TDB	0000/00/00
-	2	("6232641").PN.	USPAT;	2003/03/26
			US-PGPUB;	15:01
			EPO; JPO;	
	İ		DERWENT;	ļ
	2	/#C171010#\ DM	IBM_TDB USPAT;	2003/03/26
-	4	("6171910").PN.	US-PGPUB;	15:20
			EPO; JPO;	15:20
i			DERWENT;	
			IBM TDB	
i _	2	("6051473").PN.	USPAT;	2003/03/26
	۲	(00011/3 / .1	US-PGPUB;	15:20
			EPO; JPO;	
			DERWENT;	
	1		IBM TDB	
-	8	@ad<=20010323 and 'epi silicon' and	USPĀT;	2003/06/24
l		'raised' same 'source'	US-PGPUB;	14:42
i			EPO; JPO;	
1			DERWENT;	
			IBM_TDB	
-	9	•••• = • • • • • • • • • • • • • • • •	USPAT;	2003/06/24
		'silicon' adj1 'gate'	US-PGPUB;	14:36
			EPO; JPO;	
			DERWENT;	
		0.44.000102024 111121121 1	IBM_TDB	2002/06/24
-	24	@ad<=20010323 and 'epitaxial' adj1 'gate'	USPAT;	2003/06/24 14:36
			US-PGPUB; EPO; JPO;	14:20
			DERWENT;	
1			IBM TDB	
_	11	@ad<=20010323 and 'epi silicon' and	USPAT;	2003/06/24
	**	'raised' same 'source'	US-PGPUB;	14:42
		Tarboa bamo boaroo	EPO; JPO;	
			DERWENT;	
]		IBM TDB	
_	394	(257/756).ccls and @ad<=20010323	USPAT;	2003/06/25
		,	US-PGPUB;	08:50
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	600	438/300 and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:58
			EPO; JPO;	
1			DERWENT;	
I			IBM_TDB	<u> </u>

-	2	("6534809").PN.	USPAT;	2003/06/25
			US-PGPUB;	06:43
			EPO; JPO;	
			DERWENT;	
1	1.70		IBM_TDB	0004/00/00
-	173	@ad<=20010323 and 'epitaxial' adj1	USPAT;	2004/03/18
		'silicon' and 'elevated' same 'source'	US-PGPUB;	13:32
			EPO; JPO;	
			DERWENT;	
		0-14 00010000 3 1 45 31 451	IBM_TDB	2003/06/25
-	2	@ad<=20010323 and 'epitaxial' adj1	USPAT;	2003/06/25
		'silicon gate' and 'elevated' same 'source'	US-PGPUB;	06:46
		Source	EPO; JPO; DERWENT;	.
			IBM TDB	
_	43	<pre>@ad<=20010323 and 'gate' with 'epitaxial'</pre>	USPAT;	2003/06/25
	15	adjl 'silicon' and 'elevated' same	US-PGPUB;	07:35
		'source'	EPO; JPO;	07.33
			DERWENT;	
			IBM TDB	
-	17	@ad<=20010323 and 'transistor gate' with	USPAT;	2003/06/25
]	'epitaxial' adjl 'silicon'	US-PGPUB;	07:45
		• · · · · · · · · · · · · · · · · · · ·	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	143	@ad<=20010323 and 'transistor gate' with	USPAT;	2003/06/25
		'epitaxial'	US-PGPUB;	09:33
		-	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	238	@ad<=20010323 and 'epitaxial' adj2 'gate'	USPAT;	2003/06/25
	٠		US-PGPUB;	08:08
			EPO; JPO;	
			DERWENT;	
	_		IBM_TDB	0000/05/05
-	2	@ad<=20010323 and 'stacked gate' with	USPAT;	2003/06/25
		'epitaxial'	US-PGPUB;	08:33
		_	EPO; JPO; DERWENT;	
			IBM TDB	
_	243	(438/657).ccls. and @ad<=20010323	USPAT;	2004/03/18
	2.13	(150,007,10015; and cad 10010010	US-PGPUB;	16:48
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	225	(438/647).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:56
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	118	(257/385).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:56
	1		EPO; JPO;	
			DERWENT;	
		(057/202)1 1 0-1: 00010000	IBM_TDB	2002/06/25
-	534	(257/382).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:59
			EPO; JPO;	
			DERWENT; IBM TDB	
_	225	(438/647).ccls. and @ad<=20010323	USPAT;	2003/06/25
	223	(150,011,15015; alla Gaax-20010325	US-PGPUB;	08:57
]		EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	313	(438/300).ccls. and @ad<=20010323	USPAT;	2003/06/25
			US-PGPUB;	08:58
			EPO; JPO;	
			DERWENT;	
			IBM TDB	

	69	(257/381).ccls. and @ad<=20010323	USPAT; US-PGPUB; EPO; JPO;	2003/06/25 08:59
			DERWENT; IBM TDB	
-	244	(257/756).ccls. and @ad<=20010323	USPAT; US-PGPUB;	2003/06/25 08:59
			EPO; JPO;	08.39
			DERWENT; IBM TDB	
-	197	@ad<=20010323 and 'polysilicon gate' with	USPAT;	2003/06/25
		'epitaxial'	US-PGPUB; EPO; JPO;	09:36
			DERWENT; IBM TDB	
-	0	@ad<=20010323 and 'epitaxial silicon'	USPĀT;	2003/11/12
		with 'selected silicon'	US-PGPUB; EPO; JPO;	11:35
			DERWENT; IBM TDB	·
_	238	@ad<=20010323 and 'single' with 'poly'	USPĀT;	2003/11/12
		with 'amorphous'	US-PGPUB; EPO; JPO;	14:09
			DERWENT; IBM TDB	
_	386		USPĀT;	2003/11/12
		with 'gate'	US-PGPUB; EPO; JPO;	11:42
			DERWENT; IBM TDB	
_	88	@ad<=20010323 and 'gate electrode' with	USPĀT;	2003/11/12
		'epitaxial silicon'	US-PGPUB; EPO; JPO;	13:07
			DERWENT; IBM TDB	
-	5	@ad<=20010323 and 'epitaxial' near 'gate'	USPAT;	2003/11/12
		near 'silicon'	US-PGPUB; EPO; JPO;	13:11
			DERWENT; IBM TDB	
-	68	@ad<=20010323 and 'epitaxial' near 'gate'	USPAT;	2003/11/12
			US-PGPUB; EPO; JPO;	13:19
			DERWENT; IBM TDB	
-	14		USPAT;	2003/11/12
		near 'gate'	US-PGPUB; EPO; JPO;	13:19
			DERWENT; IBM TDB	
-	187	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2003/11/12
		near4 'gate'	US-PGPUB; EPO; JPO;	13:47
			DERWENT; IBM TDB	
-	138	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2003/11/12
		near3 'gate'	US-PGPUB; EPO; JPO;	13:20
			DERWENT; IBM TDB	
-	2	("6534809").PN.	USPAT; US-PGPUB;	2003/11/12
			EPO; JPO;	13.4/
			DERWENT; IBM TDB	
-	428	@ad<=20010323 and 'schottky gate' and	USPĀT; US-PGPUB;	2003/11/12
	1	'epitaxial'	EPO; JPO;	1 - 3 - 1 - 2
			DERWENT; IBM_TDB	
		I	·	

_	8	@ad<=20010323 and 'schottky gate' and 'epitaxial silicon'	USPAT; US-PGPUB; EPO; JPO;	2003/11/12 14:18
			DERWENT;	
_	1971	 @ad<=20010323 and 'epitaxial silicon'	IBM_TDB USPAT;	2003/11/12
	13/1	nearl 'layers'	US-PGPUB; EPO; JPO;	14:34
			DERWENT; IBM TDB	
_	13	@ad<=20010323 and 'epitaxial silicon'	USPAT;	2003/11/12
		near1 'layers' near1 'gate'	US-PGPUB;	14:34
			EPO; JPO; DERWENT;	
			IBM TDB	
-	65		USPAT;	2003/11/12
		near1 'layers' near2 'gate'	US-PGPUB; EPO; JPO;	15:11
ļ			DERWENT;	
		("5110740") PX	IBM_TDB USPAT;	2002/11/12
_	2	("5110748").PN.	USPAT; US-PGPUB;	2003/11/12 15:37
			EPO; JPO;	
			DERWENT;	,
_	1	"3959045".PN.	USPAT	2003/11/12
				15:12
-	1	"3997381".PN.	USPAT	2003/11/12 15:12
_	1	"4292730".PN.	USPAT	2003/11/12
		#4000004# PW	нераш	15:13 2003/11/12
-	1	"4888304".PN.	USPAT	15:13
-	1	"4891329".PN.	USPAT	2003/11/12
	1	"4983251".PN.	USPAT	15:14 2003/11/12
				15:14
-	1	"5006487".PN.	USPAT	2003/11/12 15:15
_	1	"5006487".PN.	USPAT	2003/11/12
		W5040504W PV	HCDAM	15:16 2003/11/12
-	1	"5013681".PN.	USPAT	15:17
-	0	("candelaria.in.").PN.	USPAT;	2003/11/12
			US-PGPUB; EPO; JPO;	15:38
			DERWENT;	
		(III) 2 of a few fac III) DV	IBM_TDB USPAT;	2003/11/12
-	0	("candelaria-jon.in.").PN.	US-PGPUB;	15:37
			EPO; JPO;	
			DERWENT; IBM TDB	
_	0	("candelaria-jon-j.in.").PN.	USPAT;	2003/11/12
			US-PGPUB;	15:38
			EPO; JPO; DERWENT;	
			IBM_TDB	0000/55/55
-	0	("Candelaria-jon-j.in.").PN.	USPAT; US-PGPUB;	2003/11/12 15:39
			EPO; JPO;	
			DERWENT;	
_	65	candelaria.in.	IBM_TDB USPAT;	2003/11/12
			US-PGPUB;	15:38
			EPO; JPO; DERWENT;	
			IBM TDB	

			_	<u> </u>
-	6	Candelaria-jon-j.in.	USPAT;	2003/11/12
			US-PGPUB;	15:39
			EPO; JPO;	
	İ		DERWENT;	
			IBM_TDB	
-	2	"20020137269"	USPAT;	2004/03/18
			US-PGPUB;	09:22
			EPO; JPO;	
			DERWENT;	i
	_		IBM_TDB	0004/00/10
-	2	"20020093054"	USPAT;	2004/03/18
			US-PGPUB;	10:09
			EPO; JPO;	
İ '			DERWENT;	
	ا م	#20010010127#	IBM_TDB	2004/03/18
-	2	"20010019137"	USPAT;	10:11
			US-PGPUB;	10:11
			EPO; JPO; DERWENT;	
			IBM TDB	·
1_	2	("6630721").PN.	USPAT;	2004/03/18
-	4	(0030721).PN.	US-PGPUB;	10:13
	[]		EPO; JPO;	
			DERWENT;	
İ			IBM TDB	i
_	2	("6433382").PN.	USPAT;	2004/03/18
		(0133302)	US-PGPUB;	10:26
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	1	"5739567".PN.	USPAT	2004/03/18
				10:19
-	1	"5627395".PN.	USPAT	2004/03/18
				10:34
-	2	("6150688").PN.	USPAT;	2004/03/18
			US-PGPUB;	10:33
			EPO; JPO;	· ·
			DERWENT;	
	_		IBM_TDB	2004/03/10
-	2	("6037202").PN.	USPAT;	2004/03/18
	[US-PGPUB; EPO; JPO;	10:34
			DERWENT;	
	[IBM TDB	
1_	22	(("5994735") or ("5886382") or	USPAT;	2004/03/18
-	""	("5780327") or ("5612563") or ("5612230")	US-PGPUB;	10:49
	[or ("5595920") or ("5578850") or	EPO; JPO;	-3
	[("5574299") or ("4447889") or ("5483094")	DERWENT;	
	[or ("5460994")).PN.	IBM TDB	
_	108	@ad<=20010323 and 'vertical' with	USPAT;	2004/03/18
1	***	'transistor' same 'epitaxial silicon'	US-PGPUB;	13:34
			EPO; JPO;	
1			DERWENT;	
			IBM TDB	
-	47	@ad<=20010323 and 'vertical' with	USPAT;	2004/03/18
1		'transistor' with 'epitaxial silicon'	US-PGPUB;	13:34
		-	EPO; JPO;	
			DERWENT;	
			IBM TDB	